

Cree® EZ290™ Gen II LEDs

Data Sheet

CxxxEZ290-Sxx00-2

Cree's EZBright® LEDs are the next generation of solid-state LED emitters that combine highly efficient InGaN materials with Cree's proprietary optical design and device technology to deliver superior value for high-intensity LEDs. The optical design maximizes light extraction efficiency and enables a Lambertian radiation pattern. Additionally, these LEDs are die attachable with conductive epoxy, solder paste or solder preforms, as well as the eutectic method. These vertically structured, low forward voltage LED chips are approximately 170 microns in height. Cree's EZ™ chips are tested for conformity to optical and electrical specifications. These LEDs are useful in a broad range of applications, such as general illumination, automotive lighting and LCD backlighting.

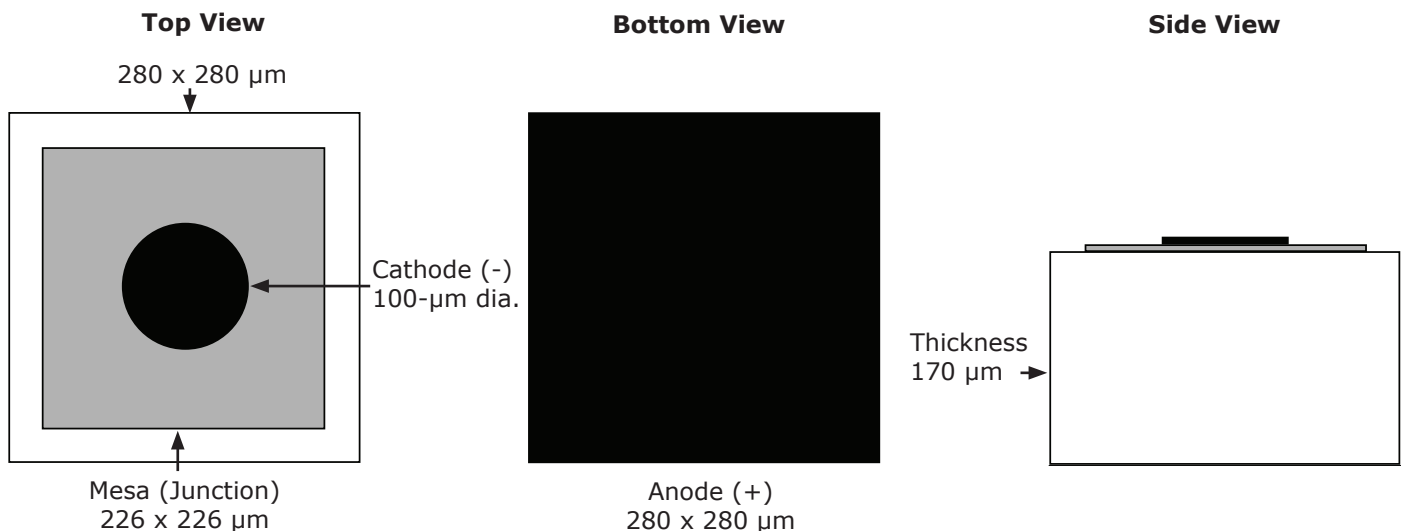
FEATURES

- EZBright LED RF Performance
 - 460 & 470 nm
 - ♦ EZ-18™ - 18 mW min. (470 nm only)
 - ♦ EZ-21™ - 21 mW min.
 - 527 nm - EZ-08™ - 8.0 mW min.
- Lambertian Radiation
- Conductive-Epoxy or Eutectic Die Attach
- Low Forward Voltage - 3.2 V Typical at 20 mA

APPLICATIONS

- LCD Backlighting
 - Mobile Appliances
 - Monitors
- LED Video Displays
- Audio Product Display Lighting
- Automotive

CxxxEZ290-Sxx00-2 Chip Diagram





Maximum Ratings at $T_A = 25^{\circ}\text{C}$ Notes 1&3		CxxxEZ290-Sxx00-2
DC Forward Current		50 mA
Peak Forward Current (1/10 duty cycle @ 1 kHz)		100 mA
LED Junction Temperature		125°C
Reverse Voltage		5 V
Operating Temperature Range		-40°C to +100°C
Storage Temperature Range		-40°C to +100°C
Electrostatic Discharge Threshold (HBM) Note 2		1000 V
Electrostatic Discharge Classification (MIL-STD-883E) Note 2		Class 2

Typical Electrical/Optical Characteristics at $T_A = 25^{\circ}\text{C}$, $I_f = 20\text{ mA}$ Note 3					
Part Number	Forward Voltage (V_f , V)			Reverse Current [$I(V_r=5\text{V})$, μA]	Full Width Half Max (λ_p , nm)
	Min.	Typ.	Max.	Max.	Typ.
C460EZ290-Sxx00-2	2.7	3.1	3.7	2	21
C470EZ290-Sxx00-2	2.7	3.1	3.7	2	22
C527EZ290-Sxx00-2	2.9	3.2	3.9	2	35

Mechanical Specifications		CxxxEZ290-Sxx00-2	
Description		Dimension	Tolerance
P-N Junction Area (μm)		226 x 226	± 25
Top Area (μm)		280 x 280	± 25
Bottom Area (μm)		280 x 280	± 25
Chip Thickness (μm)		170	± 25
Au Bond Pad Diameter (μm)		100	-15, +5
Au Bond Pad Thickness (μm)		3.0	± 1.0
Back Contact Metal Area (μm)		280 x 280	± 25
Back Contact Metal Thickness (μm) Note 4		3.0	± 0.3

Notes:

- Maximum ratings are package dependent. The above ratings were determined using a T-1 3/4 package (with Hysol OS4000 epoxy) for characterization. Ratings for other packages may differ. The forward currents (DC and Peak) are not limited by the die but by the effect of the LED junction temperature on the package. The junction temperature limit of 125°C is a limit of the T-1 3/4 package; junction temperature should be characterized in a specific package to determine limitations. Assembly processing temperature must not exceed 325°C (<5 seconds). See Cree EZBright Applications Note for assembly process information.
- Product resistance to electrostatic discharge (ESD) according to the HBM is measured by simulating ESD using a rapid avalanche energy test (RAET). The RAET procedures are designed to approximate the maximum ESD ratings shown. The RAET procedure is performed on each die. The ESD classification of Class 2 is based on sample testing according to MIL-STD-883E.
- All products conform to the listed minimum and maximum specifications for electrical and optical characteristics when assembled and operated at 20 mA within the maximum ratings shown above. Efficiency decreases at higher currents. Typical values given are within the range of average values expected by manufacturer in large quantities and are provided for information only. All measurements were made using lamps in T-1 3/4 packages (with Hysol OS4000 epoxy). Optical characteristics measured in an integrating sphere using Illuminance E.
- Specifications are subject to change without notice.



Standard Bins for CxxxEZ290-Sxx00-2

LED chips are sorted to the radiant flux and dominant wavelength bins shown. A sorted die sheet contains die from only one bin. Sorted die kit (CxxxEZ290-Sxxxx-2) orders may be filled with any or all bins (CxxxEZ290-xxxx-2) contained in the kit. All radiant flux and dominant wavelength values shown are specified at $I_f = 20$ mA.

EZ-21

C460EZ290-S2100-2

Radiant Flux	27.0 mW	C460EZ290-0213-2	C460EZ290-0214-2	C460EZ290-0215-2	C460EZ290-0216-2	
	24.0 mW	C460EZ290-0209-2	C460EZ290-0210-2	C460EZ290-0211-2	C460EZ290-0212-2	
	21.0 mW	C460EZ290-0205-2	C460EZ290-0206-2	C460EZ290-0207-2	C460EZ290-0208-2	
		455 nm	457.5 nm	460 nm	462.5 nm	465 nm
Dominant Wavelength						

EZ-18

C470EZ290-S1800-2

Radiant Flux	27.0 mW	C470EZ290-0213-2	C470EZ290-0214-2	C470EZ290-0215-2	C470EZ290-0216-2	
	24.0 mW	C470EZ290-0209-2	C470EZ290-0210-2	C470EZ290-0211-2	C470EZ290-0212-2	
	21.0 mW	C470EZ290-0205-2	C470EZ290-0206-2	C470EZ290-0207-2	C470EZ290-0208-2	
	18.0 mW	C470EZ290-0201-2	C470EZ290-0202-2	C470EZ290-0203-2	C470EZ290-0204-2	
		465 nm	467.5 nm	470 nm	472.5 nm	475 nm
Dominant Wavelength						

EZ-08

C527EZ290-S0800-2

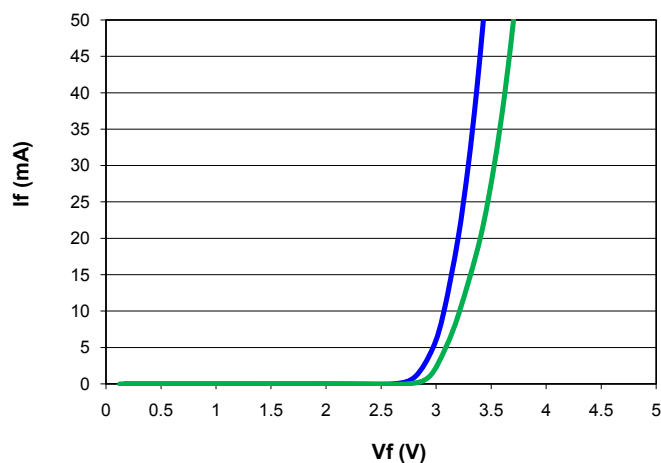
Radiant Flux	14.0 mW	C527EZ290-0210-2	C527EZ290-0211-2	C527EZ290-0212-2
	12.0 mW	C527EZ290-0207-2	C527EZ290-0208-2	C527EZ290-0209-2
	10.0 mW	C527EZ290-0204-2	C527EZ290-0205-2	C527EZ290-0206-2
	8.0 mW	C527EZ290-0201-2	C527EZ290-0202-2	C527EZ290-0203-2
	520 nm	525 nm	530 nm	535 nm
Dominant Wavelength				



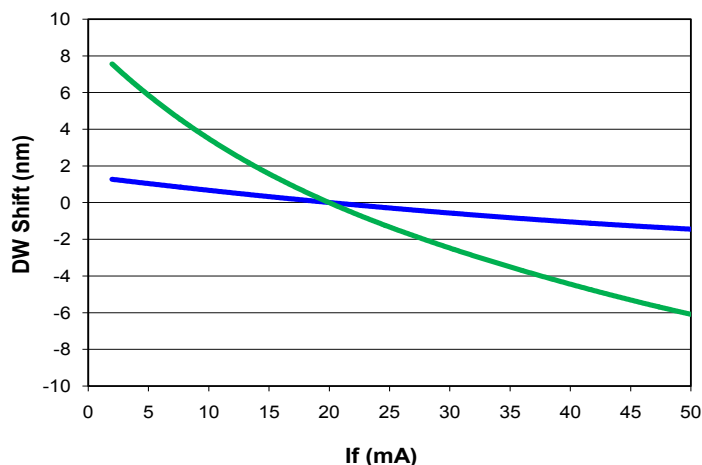
Characteristic Curves

These are representative measurements for the EZBright LED product. Actual curves will vary slightly for the various radiant flux and dominant wavelength bins.

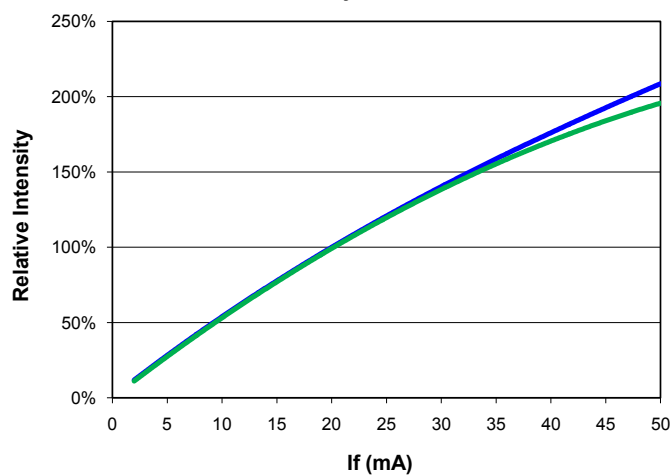
Forward Current vs. Forward Voltage



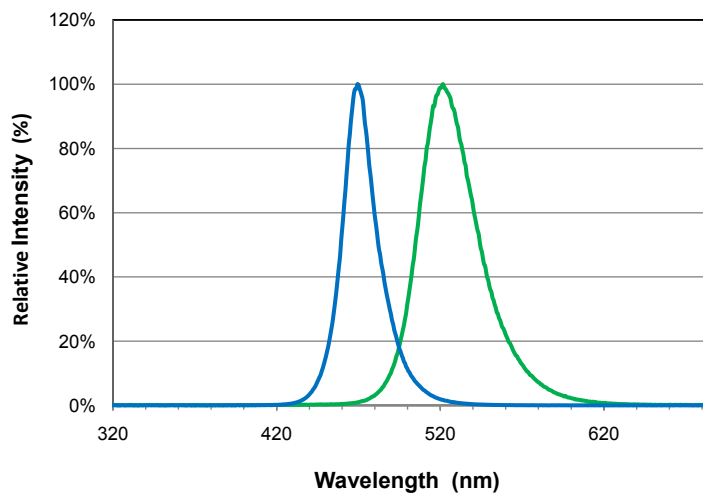
Wavelength Shift vs. Forward Current



Relative Intensity vs. Forward Current



Relative Intensity vs. Peak Wavelength





Radiation Pattern

This is a representative radiation pattern for the EZBright LED product. Actual patterns will vary slightly for each chip.

